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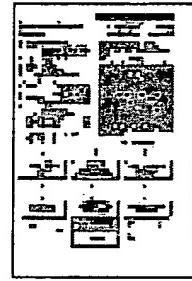
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**>Title:** JP03034466A2: VERTICAL-TYPE DOUBLE DIFFUSED MOSFET**Derwent Title:** Vertical type double diffusion MOSFET - incorporates semiconductor layer with layer having high specific resistance and layer having low specific resistance NoAbstract Dwg 1/4 [Derwent Record]**Country:** JP Japan**Kind:** A

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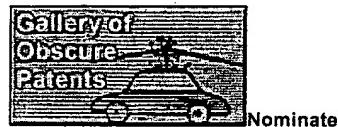
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[News, Profiles, Stocks and More about this company](#)**Published / Filed:** 1991-02-14 / 1989-06-30**Application Number:** JP1989000166786**IPC Code:** H01L 29/784;**Priority Number:** 1989-06-30 JP1989000166786**Abstract:** PURPOSE: To enable reduction of an ON-resistance without impairing an element breakdown strength by a method wherein the thickness of a second semiconductor layer of low resistivity on the side of a channel forming region is made larger than the depth of diffusion of the channel forming region.

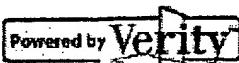
CONSTITUTION: An N-type epitaxial layer 2 in a conventional vertical-type double diffused MOSFET is constructed of two layers, a first epitaxial layer 2-1 and a second epitaxial layer 2-2. The first epitaxial layer 2-1 has the same impurity concentration as the epitaxial layer 2 in the conventional vertical-type double diffused MOSFET, while the second epitaxial layer 2-2 has a higher impurity concentration than the first epitaxial layer 2-1 and has a low resistivity. Even when the thickness of the second epitaxial layer 2-2 is made larger than the depth of diffusion of a P-type channel forming region 5, an element breakdown strength can be kept equivalent to the one of the conventional vertical-type double diffusion MOSFET.

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**Family:** None**Other Abstract Info:** DERABS C91-090279 DERCR91-090279



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